SN74CB3T3245 8 位 FET 总线开关 2.5V 和 3.3V 低压且可耐受 5V 电压的电平移位器

1 特性

- 标准 '245 型引脚排列
- 输出电压转换跟踪 V_{CC}
- 所有数据 I/O 端口上均支持以混合模式信号运行
  - 5V 输入降至 3.3V 输出的电平位移，V_{CC} 为 3.3V
  - 5V/3.3V 输入降至 2.5V 输出的电平位移，V_{CC} 为 2.5V
- 可耐受 5V 电压并支持器件加电或断电的 I/O
- 具有接近零传播延迟的双向数据流
- 低导通状态电阻 (r_{on}) 特性（r_{on} 典型值 = 5Ω）
- 低输入、输出电容可更大程度减小负载（$C_{io(OFF)}$ 典型值 = 5pF）
- 数据与控制输入提供下冲钳位二极管
- 低功耗（I_{CC} 最大值 = 40 µA）
- V_{CC} 工作范围为 2.3V 至 3.6V
- 数据 I/O 支持 0 至 5V 信号电平（0.8V、1.2V、1.5V、1.8V、2.5V、3.3V、5V）
- 控制输入可由 TTL 或 5V/3.3V CMOS 输出驱动
- I_{off} 支持局部断电模式运行
- 闩锁性能超过 250mA，符合 JESD 17 规范
- ESD 性能测试符合 JESD 22 标准
  - 2000V 人体放电模型（A114-B，II 类）
  - 1000V 充电器件模型 (C101)
- 专为低功耗便携式设备设计

2 应用

- 支持数字应用：
  - 电平转换
  - PCI 接口
  - USB 接口
  - 内存交错
  - 总线隔离

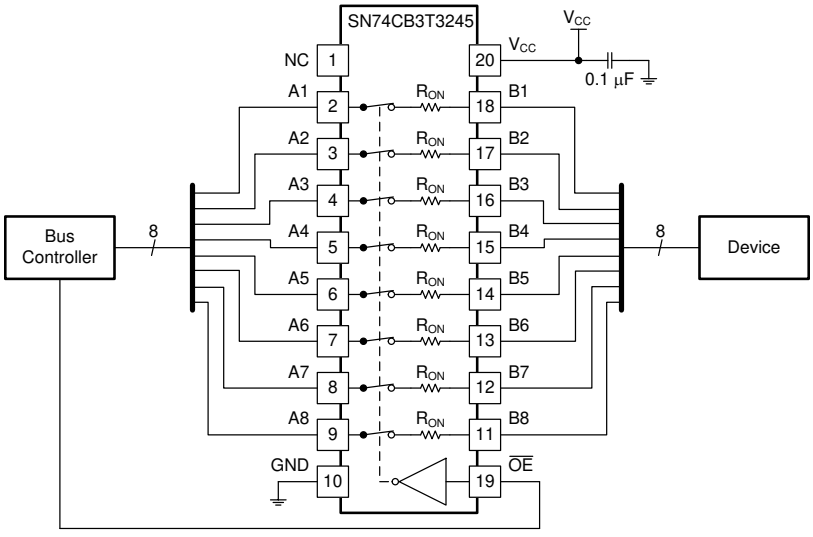
3 说明

SN74CB3T3245 是一种具备低导通状态电阻 (r_{on}) 的高速 TTL 兼容型 8 位 FET 总线开关，可实现超短传播延迟。该器件通过提供可跟踪 V_{CC} 的电压转换，完全支持在所有数据 I/O 端口上以混合模式信号运行。

封装信息

器件型号	封装 (1)	封装尺寸(2)
SN74CB3T3245DBQ	DBQ（SSOP，20）	8.65mm × 6mm
SN74CB3T3245DGV	DGV（TVSOP，20）	5.00mm × 6.4mm
SN74CB3T3245DW	DW（SOIC，20）	12.8mm × 10.3mm
SN74CB3T3245PW	PW（TSSOP，20）	6.5mm × 6.4mm
SN74CB3T3245DGS	DGS（VSSOP，20）	5.10mm × 4.9mm

(1) 有关更多信息，请参阅 节 11。
(2) 封装尺寸（长 × 宽）为标称值，并包括引脚（如适用）。



典型应用功能图

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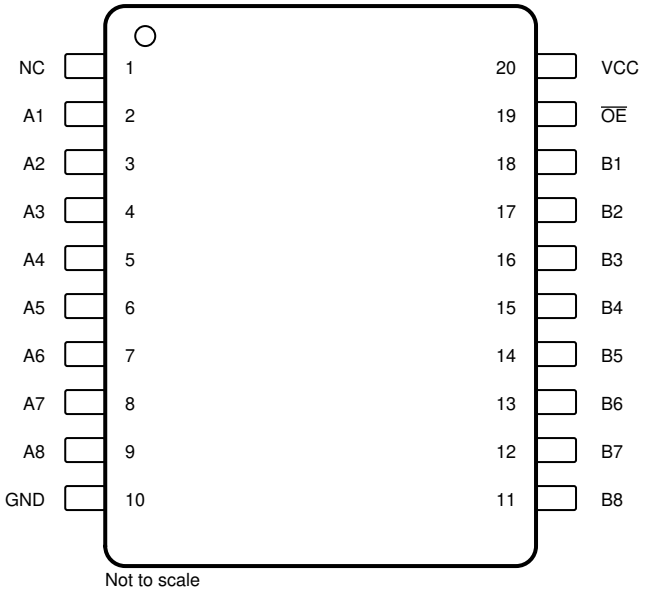
4 Pin Configuration and Functions



NC — No internal connection

图 4-1. DGS, DBQ, DGV, DW, and PW Package 20-Pin VSSOP, SSOP, TVSOP, SOIC, TSSOP Top View

表 4-1. Pin Functions

PIN		I/O	DESCRIPTION
NO.	NAME		
1	NC	—	Not internally connected
2	A1	I/O	Switch 1 A terminal
3	A2	I/O	Switch 2 A terminal
4	A3	I/O	Switch 3 A terminal
5	A4	I/O	Switch 4 A terminal
6	A5	I/O	Switch 5 A terminal
7	A6	I/O	Switch 6 A terminal
8	A7	I/O	Switch 7 A terminal
9	A8	I/O	Switch 8 A terminal
10	GND	—	Ground
11	B8	I/O	Switch 8 B terminal
12	B7	I/O	Switch 7 B terminal
13	B6	I/O	Switch 6 B terminal
14	B5	I/O	Switch 5 B terminal
15	B4	I/O	Switch 4 B terminal
16	B3	I/O	Switch 3 B terminal
17	B2	I/O	Switch 2 B terminal
18	B1	I/O	Switch 1 B terminal
19	$\overline{OE}$	I	Output enable, active low
20	V_{CC}	—	Power

5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage(2)		–0.5	7	V
V_{IN}	Control input voltage(2) (3)		–0.5	7	V
$V_{I/O}$	Switch I/O voltage(2) (3) (4)		–0.5	7	V
I_{IK}	Control input clamp current	V_{IN} < 0		–50	mA
$I_{I/OK}$	I/O port clamp current	$V_{I/O}$ < 0		–50	mA
$I_{I/O}$	ON-state switch current(5)			±128	mA
	Continuous current through V_{CC} or GND			±100	mA
T_J	Junction temperature			150	°C
T_{stg}	Storage temperature		–65	150	

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) All voltages are with respect to ground unless otherwise specified.
(3) The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
(4) V_I and V_O are used to denote specific conditions for $V_{I/O}$.
(5) I_I and I_O are used to denote specific conditions for $I_{I/O}$.

5.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001(1)	±2000	V
		Charged-device model (CDM), per JEDEC specification JESD22-C101(2)	±1000	

(1) JEDEC document JEP155 states that 500V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250V CDM allows safe manufacturing with a standard ESD control process.

5.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level control input voltage	V_{CC} = 2.3V to 2.7V	1.7	5.5	V
		V_{CC} = 2.7V to 3.6V	2	5.5	
V_{IL}	Low-level control input voltage	V_{CC} = 2.3V to 2.7V	0	0.7	V
		V_{CC} = 2.7V to 3.6V	0	0.8	
$V_{I/O}$	Data input/output voltage		0	5.5	V
T_A	Operating free-air temperature		–40	85	°C

(1) All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs.

5.4 Thermal Information

THERMAL METRIC[1]		SN74CB3T3245					UNIT
		DGS(VSSOP)	DBQ (SSOP)	DGV(TVSOP)	DW(SOIC)	PW(TSSOP)	
		20 PINS	20 PINS	20 PINS	20 PINS	20 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	127	102.4	123.7	58	112.5	°C/W

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

5.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)(1)

PARAMETER		TEST CONDITIONS		MIN	TYP(2)	MAX	UNIT
V_{IK}		V_{CC} = 3 V, I_I = – 18 mA				– 1.2	V
V_{OH}		See and 图 5-1					
I_{IN}	Control inputs	V_{CC} = 3.6 V, V_{IN} = 3.6 V to 5.5 V or GND				±10	μA
I_I		V_{CC} = 3.6 V, Switch ON, V_{IN} = V_{CC} or GND	V_I = V_{CC} – 0.7 V to 5.5 V			±20	μA
			V_I = 0.7 V to V_{CC} – 0.7 V			– 40	
			V_I = 0 to 0.7 V			±5	
I_{OZ} (3)		V_{CC} = 3.6 V, V_O = 0 to 5.5 V, V_I = 0, Switch OFF, V_{IN} = V_{CC} or GND				±10	μA
I_{off}		V_{CC} = 0, V_O = 0 to 5.5 V, V_I = 0,				10	μA
I_{CC}		V_{CC} = 3.6 V, $I_{I/O}$ = 0, Switch ON or OFF, V_{IN} = V_{CC} or GND	V_I = V_{CC} or GND			40	μA
			V_I = 5.5 V			40	
ΔI_{CC} (4)	Control inputs	V_{CC} = 3 V to 3.6 V, One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND				300	μA
C_{in}	Control inputs	V_{CC} = 3.3 V, V_{IN} = V_{CC} or GND			4		pF
$C_{io(OFF)}$		V_{CC} = 3.3 V, $V_{I/O}$ = 5.5 V, 3.3 V, or GND, Switch OFF, V_{IN} = V_{CC} or GND			5		pF
$C_{io(ON)}$		V_{CC} = 3.3 V, Switch ON, V_{IN} = V_{CC} or GND	$V_{I/O}$ = 5.5 V or 3.3 V		5		pF
			$V_{I/O}$ = GND		13		
r_{on} (5)		V_{CC} = 2.3 V, TYP at V_{CC} = 2.5 V, V_I = 0	I_O = 24 mA		5	8.5	Ω
			I_O = 16 mA		5	8.5	
		V_{CC} = 3 V, V_I = 0	I_O = 64 mA		5	7	
			I_O = 32 mA		5	7	

(1) V_{IN} and I_{IN} refer to control inputs. V_I, V_O, I_I, and I_O refer to data pins.
(2) All typical values are at V_{CC} = 3.3 V (unless otherwise noted), T_A = 25°C.
(3) For I/O ports, the parameter I_{OZ} includes the input leakage current.
(4) This is the increase in supply current for each input that is at the specified TTL voltage level, rather than V_{CC} or GND.
(5) Measured by the voltage drop between A and B terminals at the indicated current through the switch. ON-state resistance is determined by the lower of the voltages of the two (A or B) terminals.

5.6 Switching Characteristics 85C

over operating free-air temperature range (unless otherwise noted)

Parameter with Test conditions		FROM (INPUT)	TO (OUTPUT)	V_{CC}	MIN	NOM	MAX	UNIT
t_{pd}	R_L = 1GΩ, C_L = 30pF, V_{load} = 0V. Calculated Tpd with switch resistance*CL	A or B	B or A	2.5 V ± 0.2 V			0.15	ns
t_{pd}	R_L = 1GΩ, C_L = 50pF, V_{load} = 0V. Calculated Tpd with switch resistance*CL	A or B	B or A	3.3 V ± 0.3 V			0.25	ns
t_{en}	ZL: R_L = 250Ω, C_L = 30pF, V_{load} = VCC, ZH: RL = 500Ω, CL = 30pF, Vload = GND, 50ohm termination at input	OE	A or B	2.5 V ± 0.2 V			11.7	ns
t_{en}	ZL: R_L = 250Ω, C_L = 50pF, V_{load} = V_{CC} ZH: RL = 500Ω, CL = 50pF, Vload = GND, 50ohm termination at input	OE	A or B	3.3 V ± 0.3 V			8	ns
t_{dis}	LZ: R_L = 250Ω, C_L = 30pF, V_{load} = V_{CC}, Vt = 0.15V; HZ: RL = 500Ω, CL = 30pF, Vload = GND, Vt = 0.15V; 50ohm termination at input	OE	A or B	2.5 V ± 0.2 V	1		8	ns

5.6 Switching Characteristics 85C（续）

over operating free-air temperature range (unless otherwise noted)

Parameter with Test conditions		FROM (INPUT)	TO (OUTPUT)	V_{CC}	MIN	NOM	MAX	UNIT
t_{dis}	LZ: R_L = 250 Ω, C_L = 50pF, V_{load} = V_{CC}, Vt = 0.3V; HZ: RL = 500 Ω, CL = 50pF, Vload = GND, Vt = 0.3V; 50ohm termination at input	OE	A or B	3.3 V ± 0.3 V	1		8.8	ns

5.7 Typical Characteristics

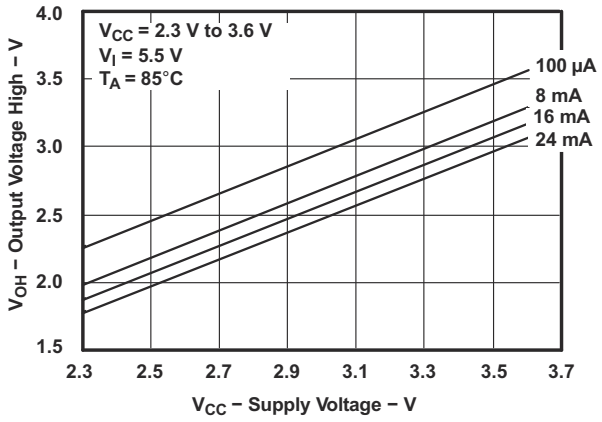


图 5-1. V_{OH} vs V_{CC}

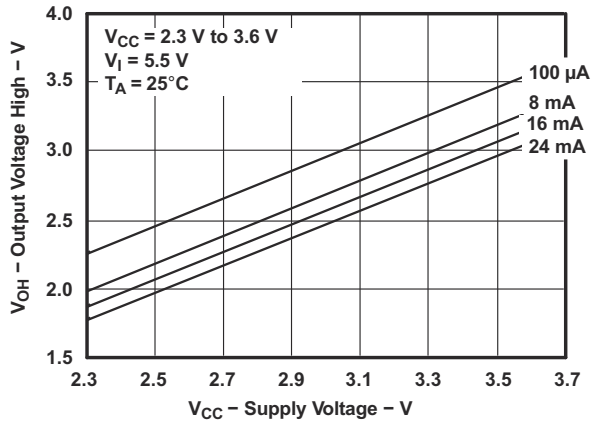


图 5-2. V_{OH} vs V_{CC}

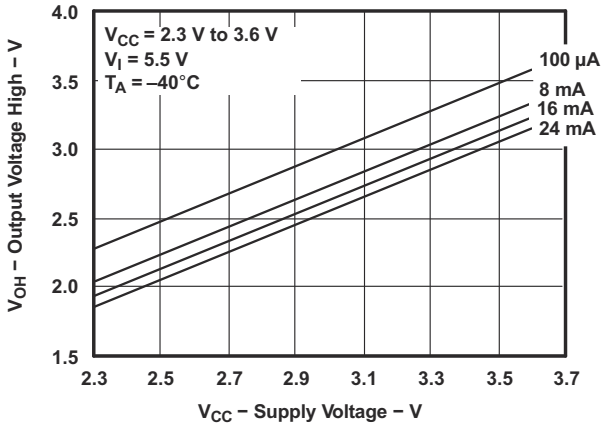
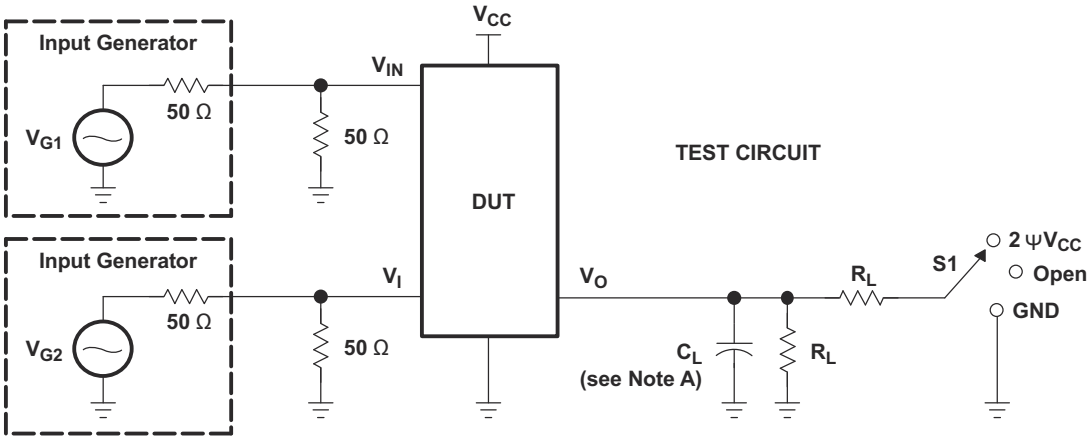
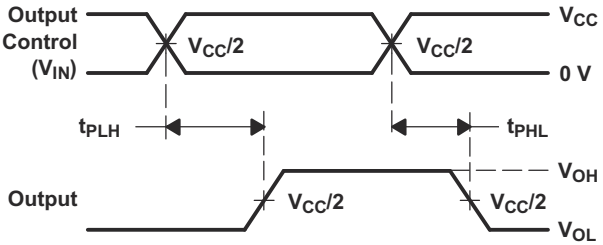


图 5-3. V_{OH} vs V_{CC}

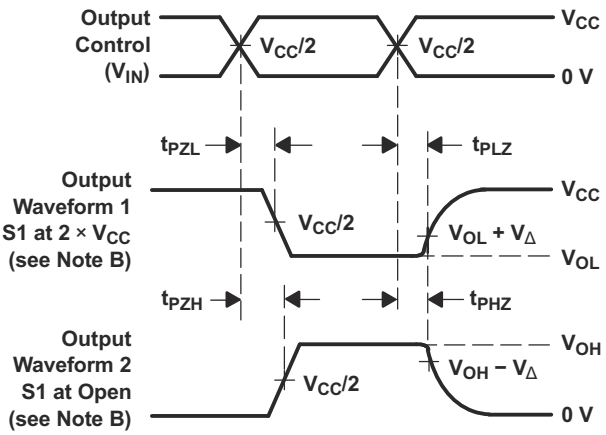
6 Parameter Measurement Information



TEST	V_{CC}	S1	R_L	V_I	C_L	V_Δ
$t_{pd(s)}$	2.5 V ± 0.2 V 3.3 V ± 0.3 V	Open Open	500 Ω 500 Ω	3.6 V or GND 5.5 V or GND	30 pF 50 pF	
t_{PLZ}/t_{PZL}	2.5 V ± 0.2 V 3.3 V ± 0.3 V	2 × V_{CC} 2 × V_{CC}	500 Ω 500 Ω	GND GND	30 pF 50 pF	0.15 V 0.3 V
t_{PHZ}/t_{PZH}	2.5 V ± 0.2 V 3.3 V ± 0.3 V	Open Open	500 Ω 500 Ω	3.6 V 5.5 V	30 pF 50 pF	0.15 V 0.3 V



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES ($t_{pd(s)}$)



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time, with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as $t_{pd(s)}$. The tpd propagation delay is the calculated RC time constant of the typical ON-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).
H. All parameters and waveforms are not applicable to all devices.

图 6-1. Test Circuit and Voltage Waveforms

7 Detailed Description

7.1 Overview

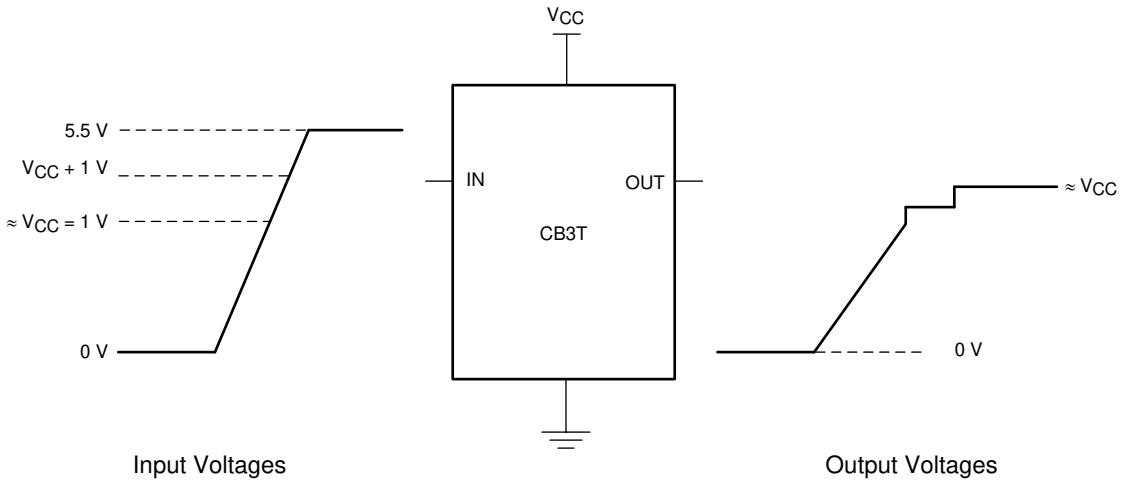
The SN74CB3T3245 device is a high-speed TTL-compatible FET bus switch with low ON-state resistance (r_{on}), allowing for minimal propagation delay. The device fully supports mixed-mode signal operation on all data I/O ports by providing voltage translation that tracks V_{CC}. The SN74CB3T3245 device supports systems using 5-V TTL, 3.3-V LVTTL, and 2.5-V CMOS switching standards, as well as user-defined switching levels (see 图 7-1).

The SN74CB3T3245 device is an 8-bit bus switch with a single output-enable ($\overline{OE}$) input and a standard '245 pinout. When $\overline{OE}$ is low, the 8-bit bus switch is ON, and the A port is connected to the B port, allowing bidirectional data flow between ports. When $\overline{OE}$ is high, the 8-bit bus switch is OFF, and a high-impedance state exists between the A and B ports.

This device is fully specified for partial-power-down applications using I_{off}. The I_{off} feature certifies that damaging current does not backflow through the device when the device is powered down. The device has isolation during power off.

To establish the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

7.2 Functional Block Diagram



If the input high voltage (V_{IH}) level is greater than or equal to V_{CC} + 1V, and less than or equal to 5.5V, the output high voltage (V_{OH}) level is equal to approximately the V_{CC} voltage level.

图 7-1. Typical DC Voltage Translation Characteristics

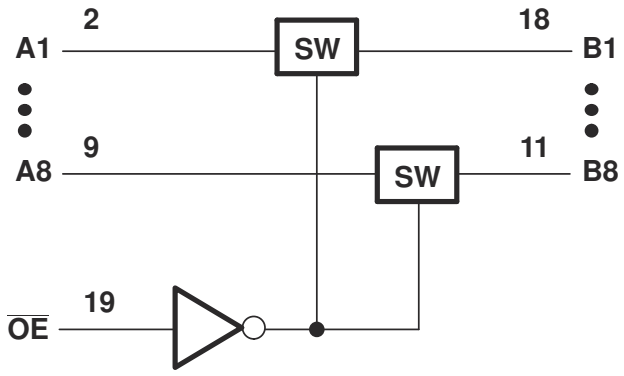
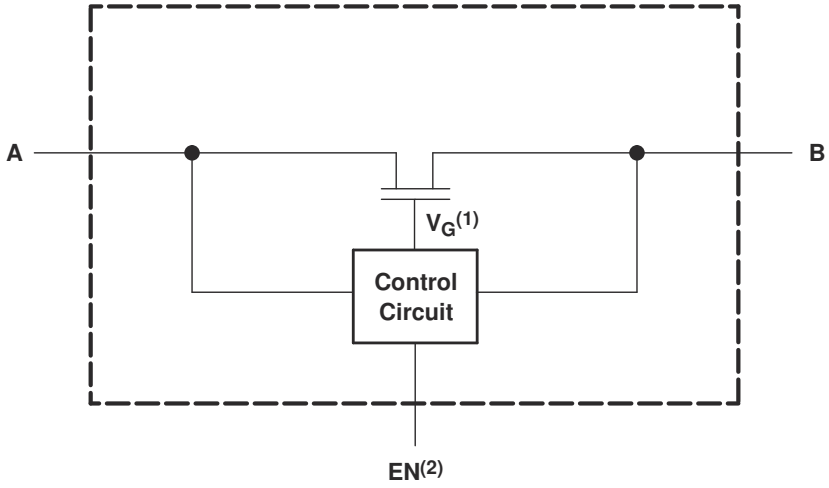


图 7-2. Logic Diagram (Positive Logic)



1) Gate Voltage (V_G) is approximately equal to $V_{CC} + V_T$ when the switch is ON and $V_I > (V_{CC} + V_T)$.
2) EN is the internal enable signal applied to the switch.

图 7-3. Simplified Schematic, Each FET Switch (SW)

7.3 Feature Description

The SN74CB3T3245 device uses the standard '245-type pinout. The output voltage tracks V_{CC}, allowing for easy down-translation. The device is prime for low-power portable equipment.

Mixed-mode signal operation is supported on all data I/O ports. 5V input down to 3.3V output level shift with 3.3V V_{CC} and 5V/3.3V input down to 2.5V output level shift With 2.5V V_{CC} are possible due to overvoltage tolerant inputs.

This part is friendly to partial power down systems. The I/Os are 5V-tolerant with the device powered up or powered down and I_{off} supports partial-power-down mode operation.

The SN74CB3T3245 has a bidirectional data flow with near-zero propagation delay.

The SN74CB3T3245 has low ON-state resistance (r_{on}) characteristics (r_{on} = 5Ω typical).

The SN74CB3T3245 has both low input and output capacitance minimizes loading ($C_{io(OFF)}$ = 5pF typical).

Data and control inputs provide undershoot clamp diodes.

The SN74CB3T3245 has low power consumption (I_{CC} = 40 μA Maximum).

The SN74CB3T3245 has a V_{CC} operating range from 2.3V to 3.6V.

The data I/Os support 0V to 5V signaling levels (0.8V, 1.2V, 1.5V, 1.8V, 2.5V, 3.3V, 5V).

Control inputs can be driven by TTL or 5V/3.3V CMOS outputs.

7.4 Device Functional Modes

表 7-1 lists the functional modes of the SN74CB3T3245.

表 7-1. Function Table

INPUT $\overline{OE}$	INPUT/OUTPUT A	FUNCTION
L	B	A port = B port
H	Z	Disconnect

8 Application and Implementation

备注

以下应用部分中的信息不属于 TI 器件规格的范围，TI 不担保其准确性和完整性。TI 的客 户应负责确定器件是否适用于其应用。客户应验证并测试其设计，以确保系统功能。

8.1 Application Information

This application is specifically to connect a 5V bus to a 3.3V device. Assume that communication in this particular application is one-directional, going from the bus controller to the device.

8.2 Typical Application

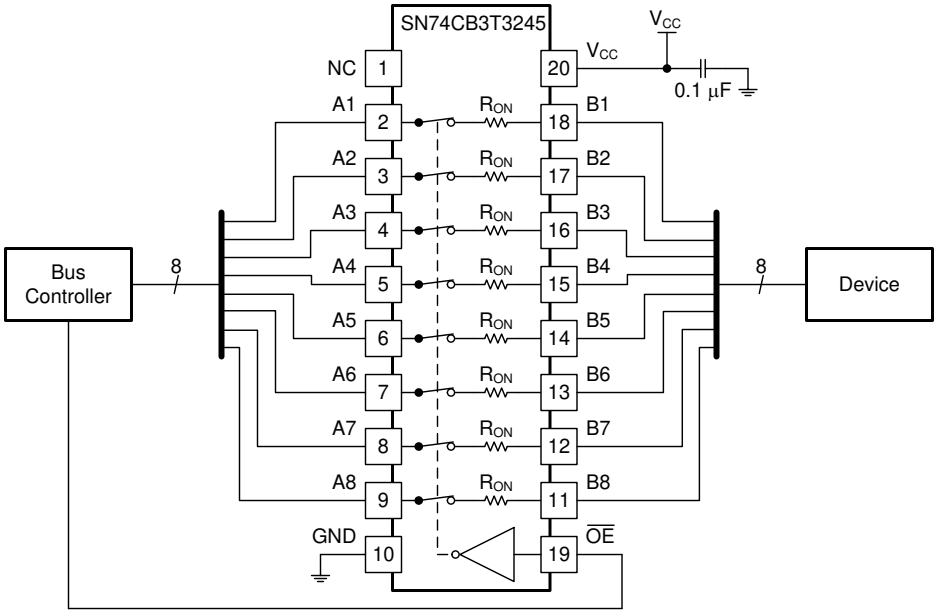


图 8-1. Typical Application Schematic

8.2.1 Design Requirements

This device uses CMOS technology and has balanced output drive. Take care to avoid bus contention because bus contention can drive currents that can exceed maximum limits.

Because this design is for down-translating voltage, no pullup resistors are required.

8.2.2 Detailed Design Procedure

1. Recommended input conditions
   - Specified high and low levels. See (V_{IH} and V_{IL}) in *Recommended Operating Conditions*.
   - Inputs are overvoltage tolerant allowing them to go as high as 7V at any valid V_{CC}.
2. Recommend output conditions
   - Load currents must not exceed 128mA on each channel.

8.2.3 Application Curves

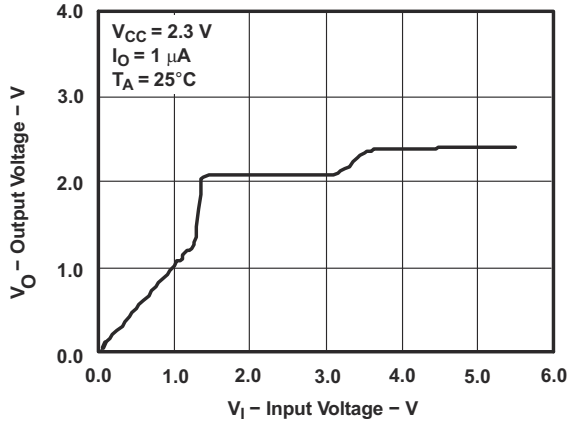


图 8-2. Data Output Voltage vs Data Input Voltage

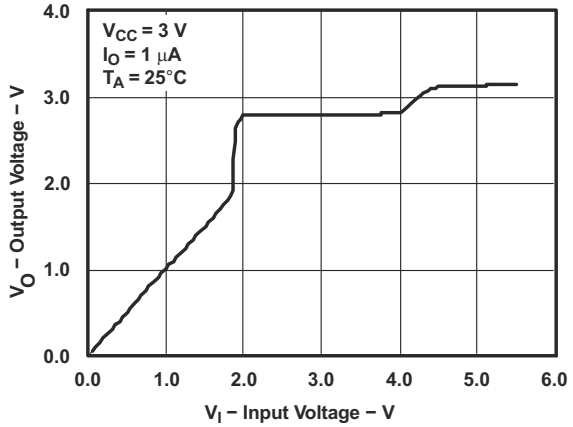


图 8-3. Data Output Voltage vs Data Input Voltage

8.3 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions*.

Each V_{CC} terminal must have a good bypass capacitor to prevent power disturbance. For devices with a single supply, TI recommends a 0.1 μF bypass capacitor. If there are multiple pins labeled V_{CC}, then TI recommends a 0.01 μF or 0.022 μF capacitor for each V_{CC} because the V_{CC} pins are tied together internally. For devices with dual supply pins operating at different voltages, for example V_{CC} and V_{DD}, a 0.1 μF bypass capacitor is recommended for each supply pin. Paralleling multiple bypass capacitors to reject different frequencies of noise is acceptable. 0.1 μF and 1 μF capacitors are commonly used in parallel. For best results, install the bypass capacitor as close to the power terminal.

8.4 Layout

8.4.1 Layout Guidelines

Reflections and matching are closely related to the loop antenna theory but are different enough to be discussed separately from the theory. When a PCB trace turns a corner at a 90° angle, a reflection can occur. A reflection occurs primarily because of the change of width of the trace. At the apex of the turn, the trace width increases to 1.414 times the width. This increase upsets the transmission-line characteristics, especially the distributed capacitance and self‐inductance of the trace which results in the reflection. Not all PCB traces can be straight and therefore some traces must turn corners. 图 8-4 shows progressively better techniques of rounding corners. Only the last example (BEST) maintains constant trace width and minimizes reflections.

8.4.2 Layout Example

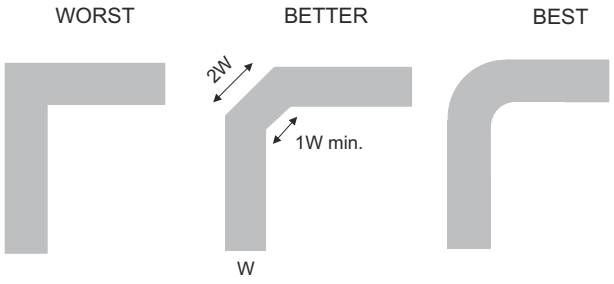


图 8-4. Trace Example

9 Device and Documentation Support

9.1 Documentation Support

9.1.1 Related Documentation

For related documentation, see the following:

Texas Instruments, *Implications of Slow or Floating CMOS Inputs* application note

9.2 接收文档更新通知

要接收文档更新通知，请导航至 ti.com 上的器件产品文件夹。点击*通知* 进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

9.3 支持资源

TI E2E™ 中文支持论坛是工程师的重要参考资料，可直接从专家处获得快速、经过验证的解答和设计帮助。搜索现有解答或提出自己的问题，获得所需的快速设计帮助。

链接的内容由各个贡献者“按原样”提供。这些内容并不构成 TI 技术规范，并且不一定反映 TI 的观点；请参阅 TI 的使用条款。

9.4 Trademarks

TI E2E™ is a trademark of Texas Instruments.
所有商标均为其各自所有者的财产。

9.5 静电放电警告

静电放电 (ESD) 会损坏这个集成电路。德州仪器 (TI) 建议通过适当的预防措施处理所有集成电路。如果不遵守正确的处理和安装程序，可能会损坏集成电路。

ESD 的损坏小至导致微小的性能降级，大至整个器件故障。精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

9.6 术语表

TI 术语表　　本术语表列出并解释了术语、首字母缩略词和定义。

10 Revision History

注：以前版本的页码可能与当前版本的页码不同

Changes from Revision C (May 2018) to Revision D (May 2025)	Page
• 更新了整个文档中的表格、图和交叉参考的编号格式	1
• 通篇添加了 DGS 封装	1
• Updated specs in the *Switching Characteristics* table	4
• Added the latest information and new package to the *Thermal Information* table	4

Changes from Revision B (June 2015) to Revision C (May 2018)	Page
• Changed the pin out image appearance	3
• Changed I_O = 1mA To: I_O = 1μA in 图 8-2 and 图 8-3	12

Changes from Revision A (August 2012) to Revision B (June 2015)	Page
• 添加了*应用*、*器件信息* 表、*引脚配置和功能* 部分、*ESD 等级* 表、*特性说明* 部分、*器件功能模式*、*应用和实施* 部分、*电源相关建议* 部分、*布局* 部分、*器件和文档支持* 部分以及*机械、封装和可订购信息* 部分	1

- 删除了 *订购信息* 表。 1

Changes from Revision * (March 2005) to Revision A (August 2012)	Page
• Updated graphic note and picture in Figure 1	9

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package | Pins	Package qty | Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
SN74CB3T3245DBQR	Active	Production	SSOP (DBQ) | 20	2500 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	CB3T3245
SN74CB3T3245DBQR.A	Active	Production	SSOP (DBQ) | 20	2500 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	CB3T3245
SN74CB3T3245DBQR.B	Active	Production	SSOP (DBQ) | 20	2500 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	CB3T3245
SN74CB3T3245DBQRG4	Active	Production	SSOP (DBQ) | 20	2500 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	CB3T3245
SN74CB3T3245DBQRG4.A	Active	Production	SSOP (DBQ) | 20	2500 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	CB3T3245
SN74CB3T3245DBQRG4.B	Active	Production	SSOP (DBQ) | 20	2500 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	CB3T3245
SN74CB3T3245DGSR	Active	Production	VSSOP (DGS) | 20	5000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	3OJS
SN74CB3T3245DGVR	Active	Production	TVSOP (DGV) | 20	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	KS245
SN74CB3T3245DGVR.A	Active	Production	TVSOP (DGV) | 20	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	KS245
SN74CB3T3245DGVR.B	Active	Production	TVSOP (DGV) | 20	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	KS245
SN74CB3T3245DGVRG4	Active	Production	TVSOP (DGV) | 20	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	KS245
SN74CB3T3245DGVRG4.A	Active	Production	TVSOP (DGV) | 20	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	KS245
SN74CB3T3245DGVRG4.B	Active	Production	TVSOP (DGV) | 20	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	KS245
SN74CB3T3245DW	Active	Production	SOIC (DW) | 20	25 | TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CB3T3245
SN74CB3T3245DW.B	Active	Production	SOIC (DW) | 20	25 | TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CB3T3245
SN74CB3T3245DWG4	Active	Production	SOIC (DW) | 20	25 | TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CB3T3245
SN74CB3T3245DWR	Active	Production	SOIC (DW) | 20	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CB3T3245
SN74CB3T3245DWR.B	Active	Production	SOIC (DW) | 20	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CB3T3245
SN74CB3T3245PW	Obsolete	Production	TSSOP (PW) | 20	-	-	Call TI	Call TI	-40 to 85	KS245
SN74CB3T3245PWR	Active	Production	TSSOP (PW) | 20	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	KS245
SN74CB3T3245PWR.A	Active	Production	TSSOP (PW) | 20	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	KS245
SN74CB3T3245PWR.B	Active	Production	TSSOP (PW) | 20	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	KS245
SN74CB3T3245PWRG4	Active	Production	TSSOP (PW) | 20	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	KS245
SN74CB3T3245PWRG4.A	Active	Production	TSSOP (PW) | 20	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	KS245
SN74CB3T3245PWRG4.B	Active	Production	TSSOP (PW) | 20	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	KS245

(1) **Status:** For more details on status, see our product life cycle.

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

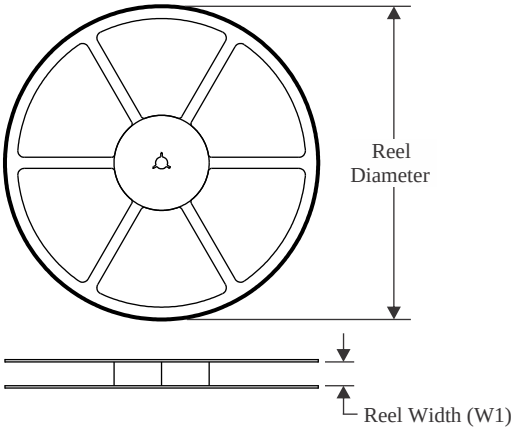
Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

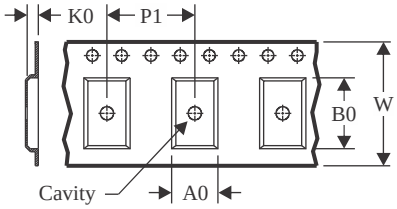
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

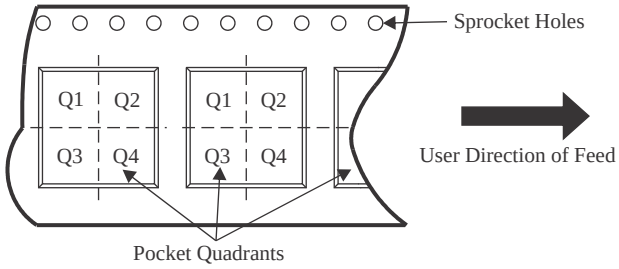


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

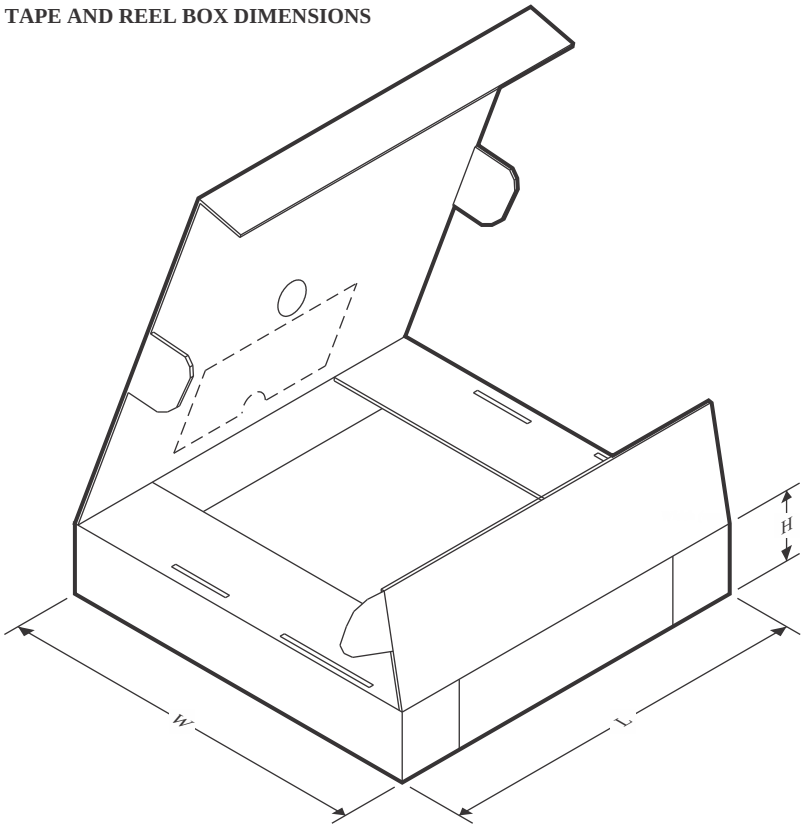
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74CB3T3245DBQR	SSOP	DBQ	20	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
SN74CB3T3245DBQRG4	SSOP	DBQ	20	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
SN74CB3T3245DGSR	VSSOP	DGS	20	5000	330.0	16.4	5.4	5.4	1.45	8.0	16.0	Q1
SN74CB3T3245DGVR	TVSOP	DGV	20	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74CB3T3245DGVRG4	TVSOP	DGV	20	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74CB3T3245DWR	SOIC	DW	20	2000	330.0	24.4	10.8	13.3	2.7	12.0	24.0	Q1
SN74CB3T3245PWR	TSSOP	PW	20	2000	330.0	16.4	6.95	7.0	1.4	8.0	16.0	Q1
SN74CB3T3245PWRG4	TSSOP	PW	20	2000	330.0	16.4	6.95	7.0	1.4	8.0	16.0	Q1

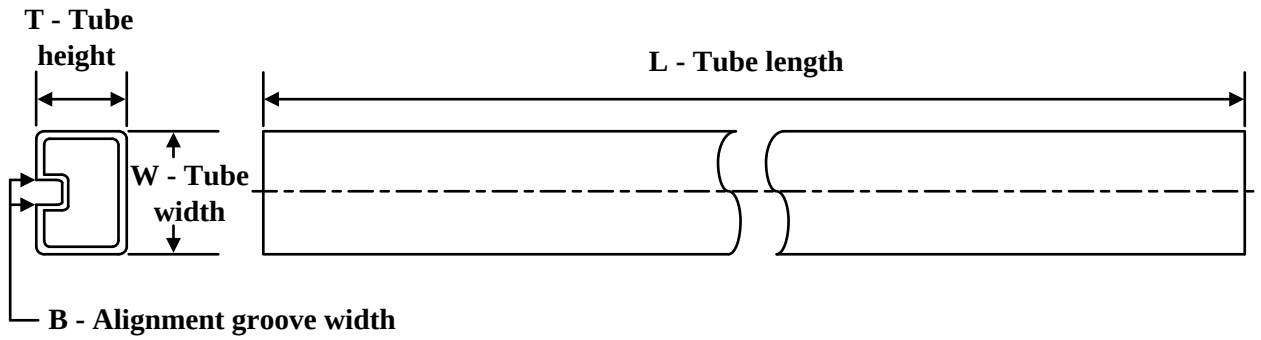
TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74CB3T3245DBQR	SSOP	DBQ	20	2500	353.0	353.0	32.0
SN74CB3T3245DBQRG4	SSOP	DBQ	20	2500	353.0	353.0	32.0
SN74CB3T3245DGSR	VSSOP	DGS	20	5000	353.0	353.0	32.0
SN74CB3T3245DGVR	TVSOP	DGV	20	2000	353.0	353.0	32.0
SN74CB3T3245DGVRG4	TVSOP	DGV	20	2000	353.0	353.0	32.0
SN74CB3T3245DWR	SOIC	DW	20	2000	356.0	356.0	45.0
SN74CB3T3245PWR	TSSOP	PW	20	2000	353.0	353.0	32.0
SN74CB3T3245PWRG4	TSSOP	PW	20	2000	353.0	353.0	32.0

TUBE



*All dimensions are nominal

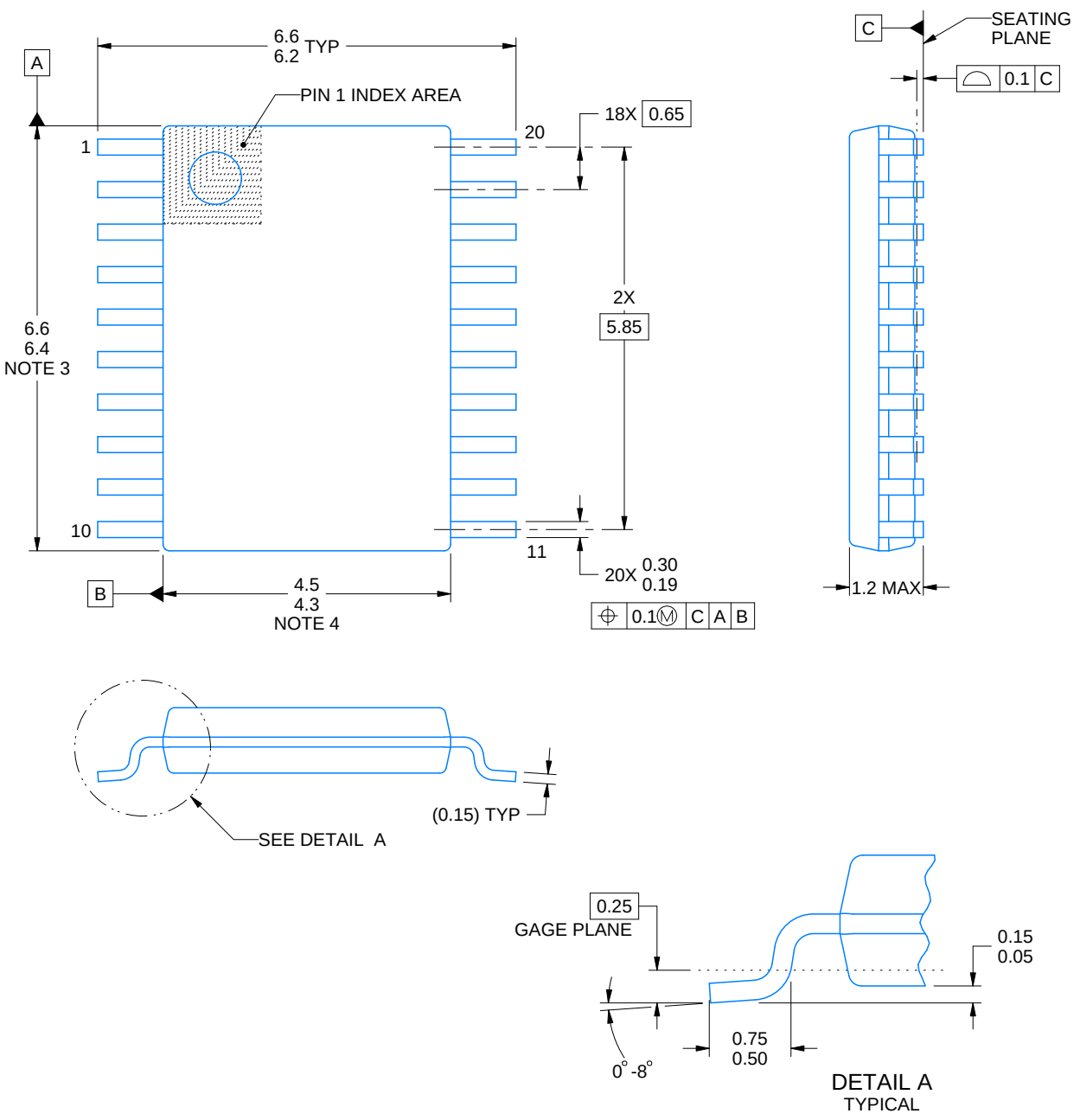
Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
SN74CB3T3245DW	DW	SOIC	20	25	507	12.83	5080	6.6
SN74CB3T3245DW.B	DW	SOIC	20	25	507	12.83	5080	6.6
SN74CB3T3245DWG4	DW	SOIC	20	25	507	12.83	5080	6.6

PACKAGE OUTLINE

PW0020A

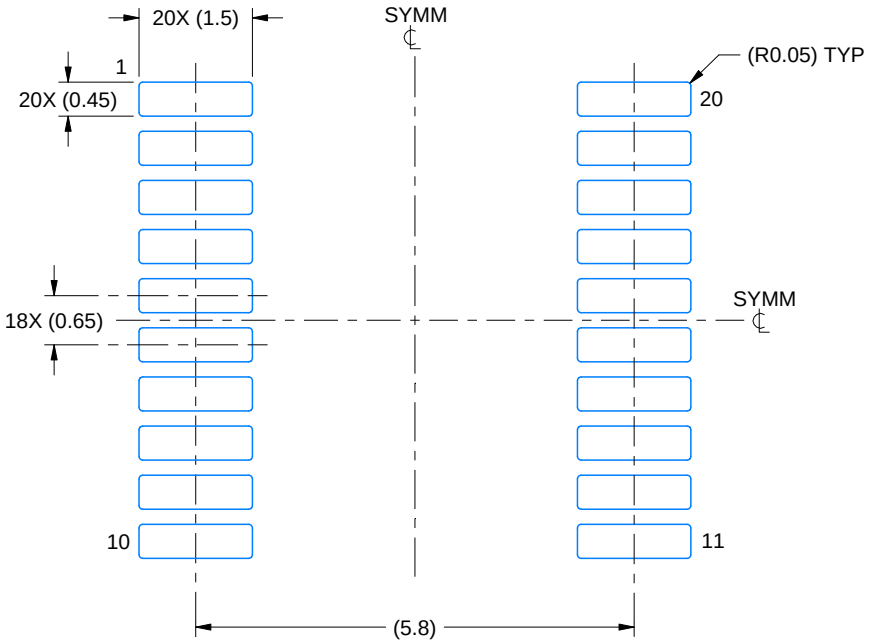
TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153.



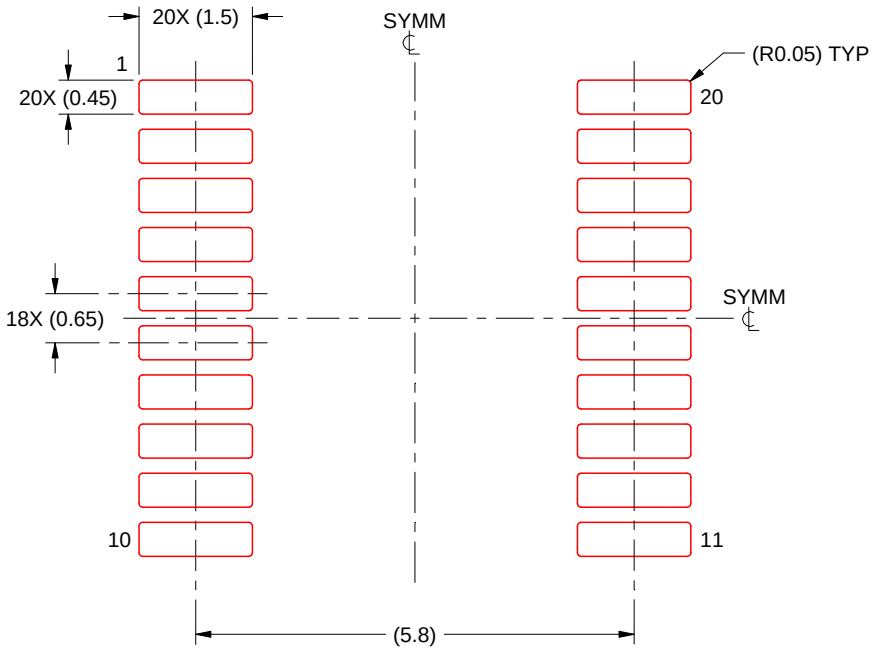
LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X

SOLDER MASK DETAILS

4220206/A 02/2017

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

4220206/A 02/2017

NOTES: (continued)

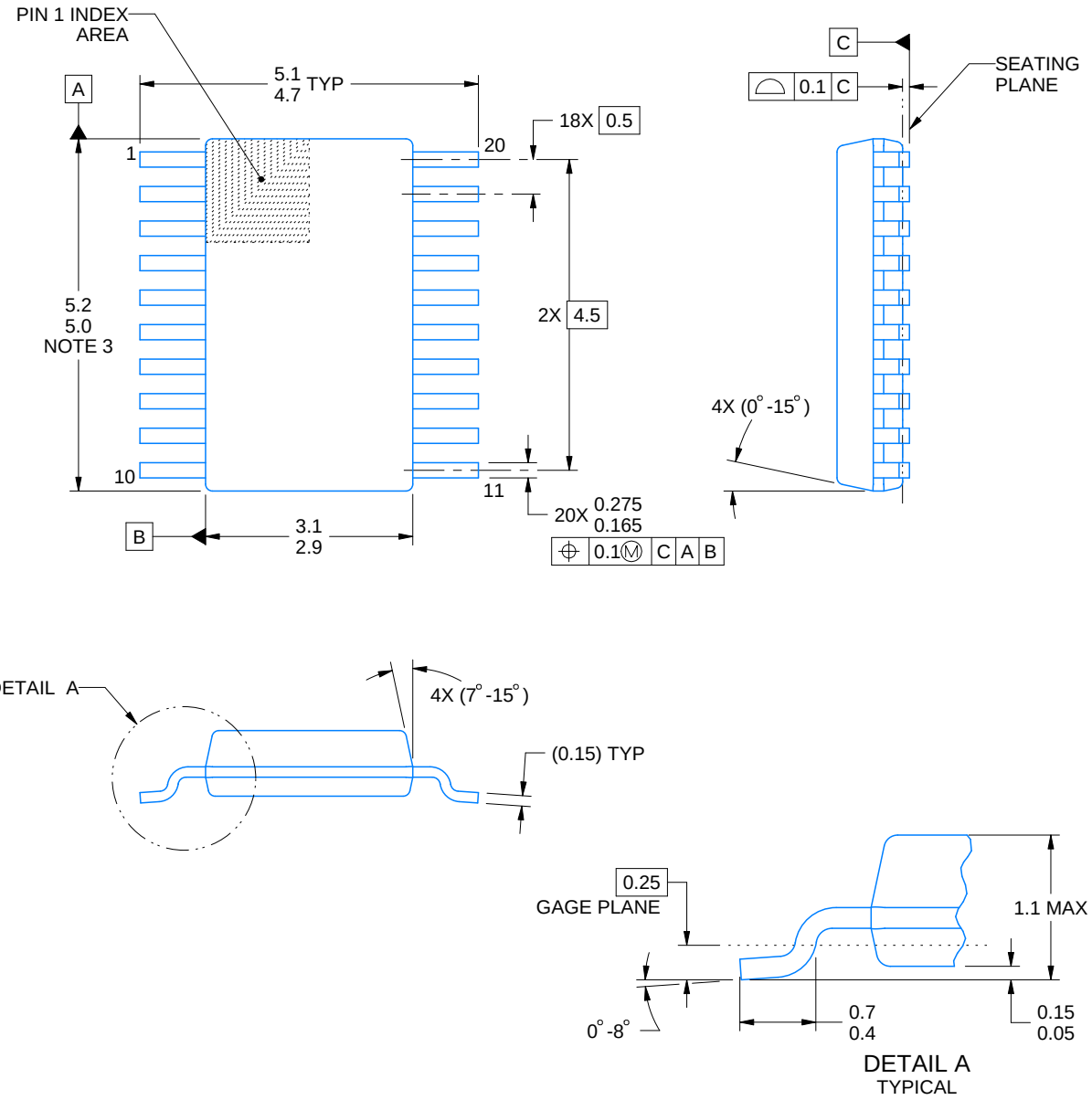
8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

PACKAGE OUTLINE

DGS0020A

VSSOP - 1.1 mm max height

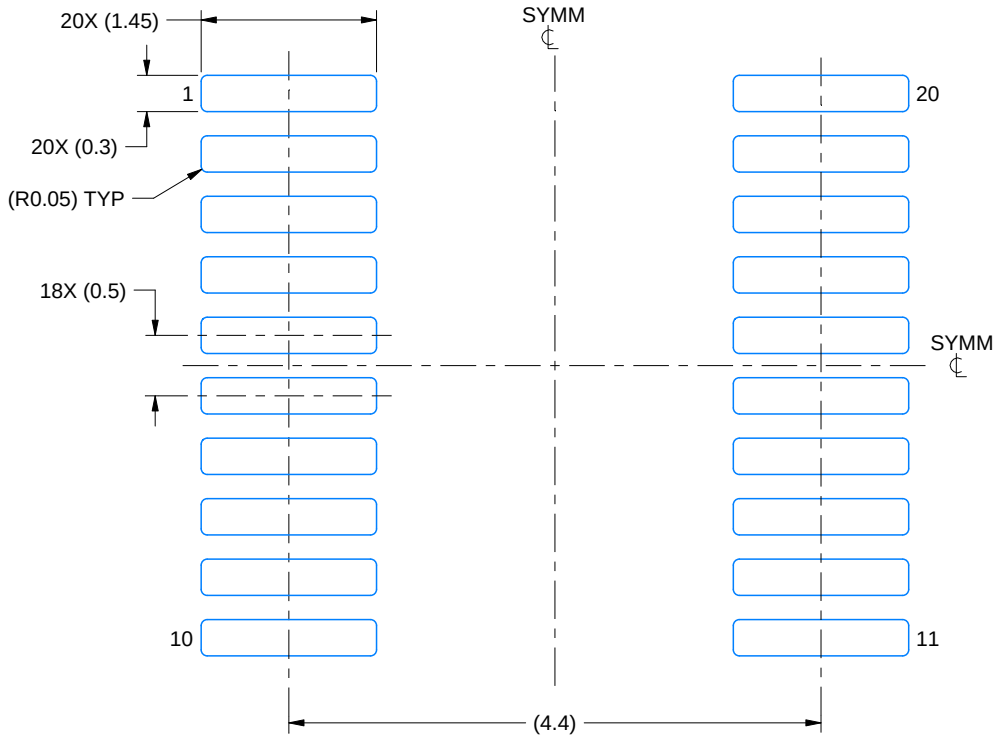
SMALL OUTLINE PACKAGE



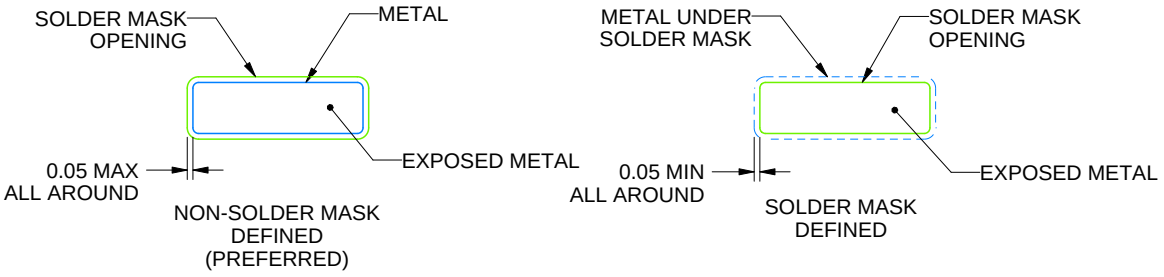
PowerPAD is a trademark of Texas Instruments.

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. No JEDEC registration as of September 2020.
5. Features may differ or may not be present.



LAND PATTERN EXAMPLE
SCALE: 16X

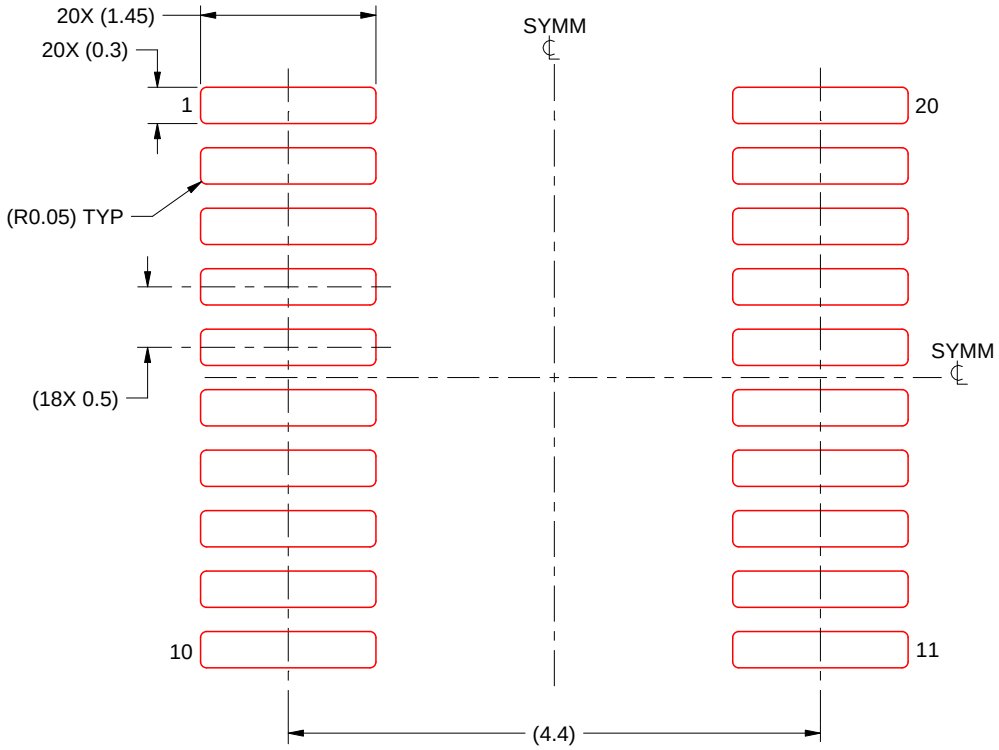


SOLDER MASK DETAILS

4226367/A 10/2020

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.
8. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature numbers SLMA002 (www.ti.com/lit/slma002) and SLMA004 (www.ti.com/lit/slma004).
9. Size of metal pad may vary due to creepage requirement.
10. Vias are optional depending on application, refer to device data sheet. It is recommended that vias under paste be filled, plugged or tented.



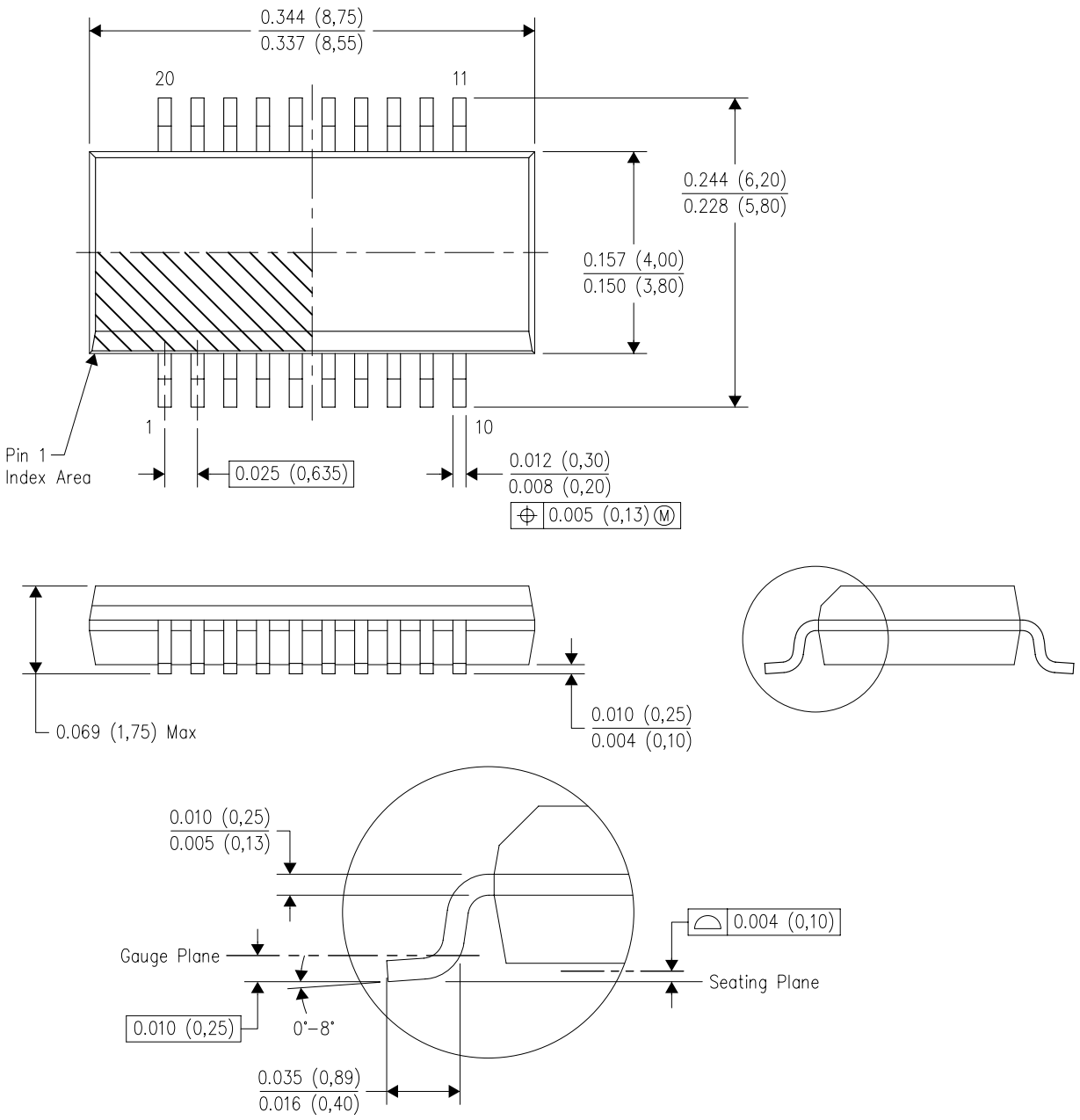
SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 16X

4226367/A 10/2020

NOTES: (continued)

11. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
12. Board assembly site may have different recommendations for stencil design.

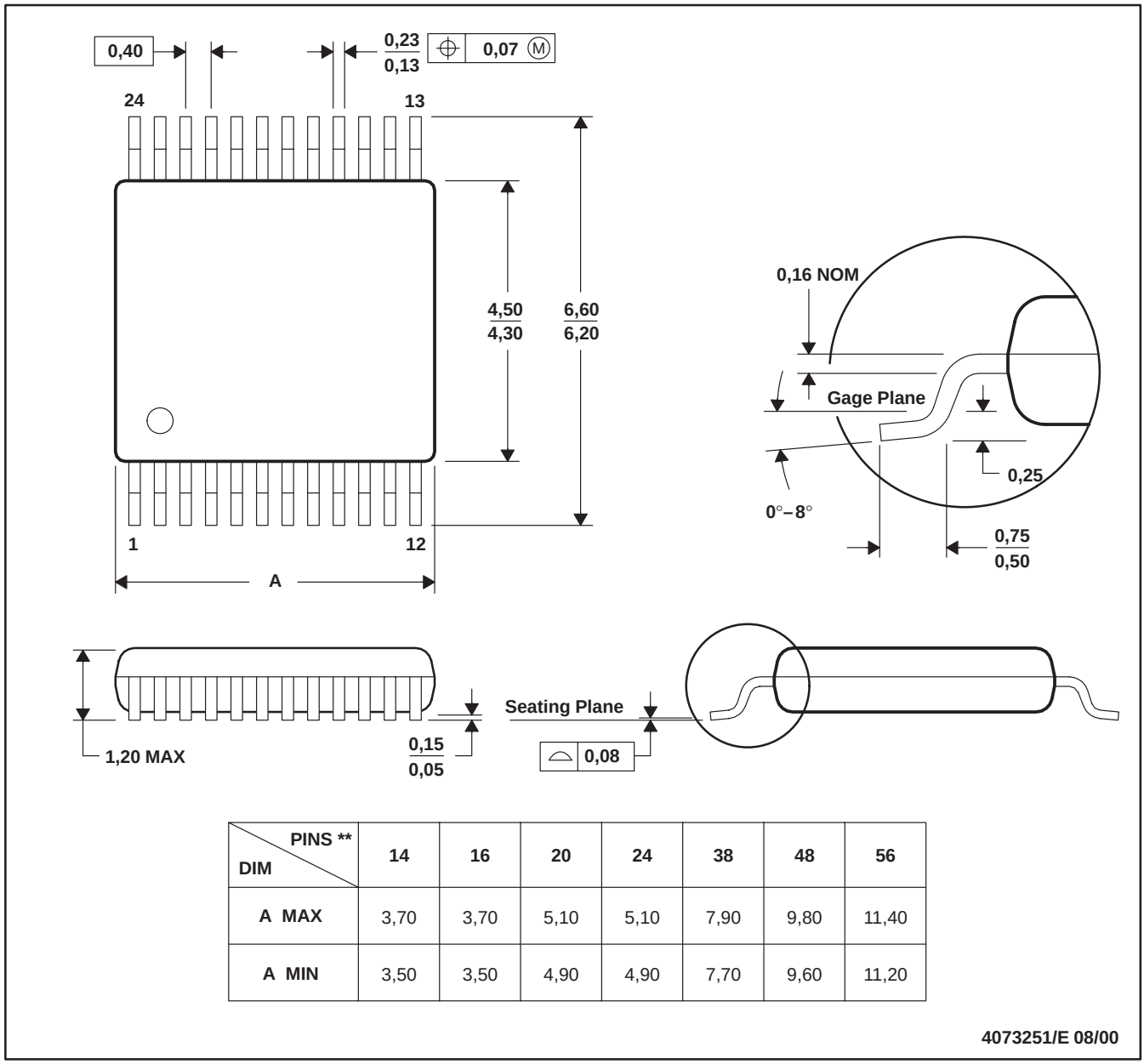
DBQ (R–PDSO–G20) PLASTIC SMALL–OUTLINE PACKAGE



NOTES:
A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15) per side.
D. Falls within JEDEC MO–137 variation AD.

DGV (R-PDSO-G)** **PLASTIC SMALL-OUTLINE**

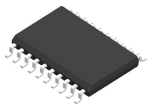
24 PINS SHOWN



DIM \ PINS **	14	16	20	24	38	48	56
A MAX	3,70	3,70	5,10	5,10	7,90	9,80	11,40
A MIN	3,50	3,50	4,90	4,90	7,70	9,60	11,20

4073251/E 08/00

NOTES: A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15 per side.
D. Falls within JEDEC: 24/48 Pins – MO-153
14/16/20/56 Pins – MO-194

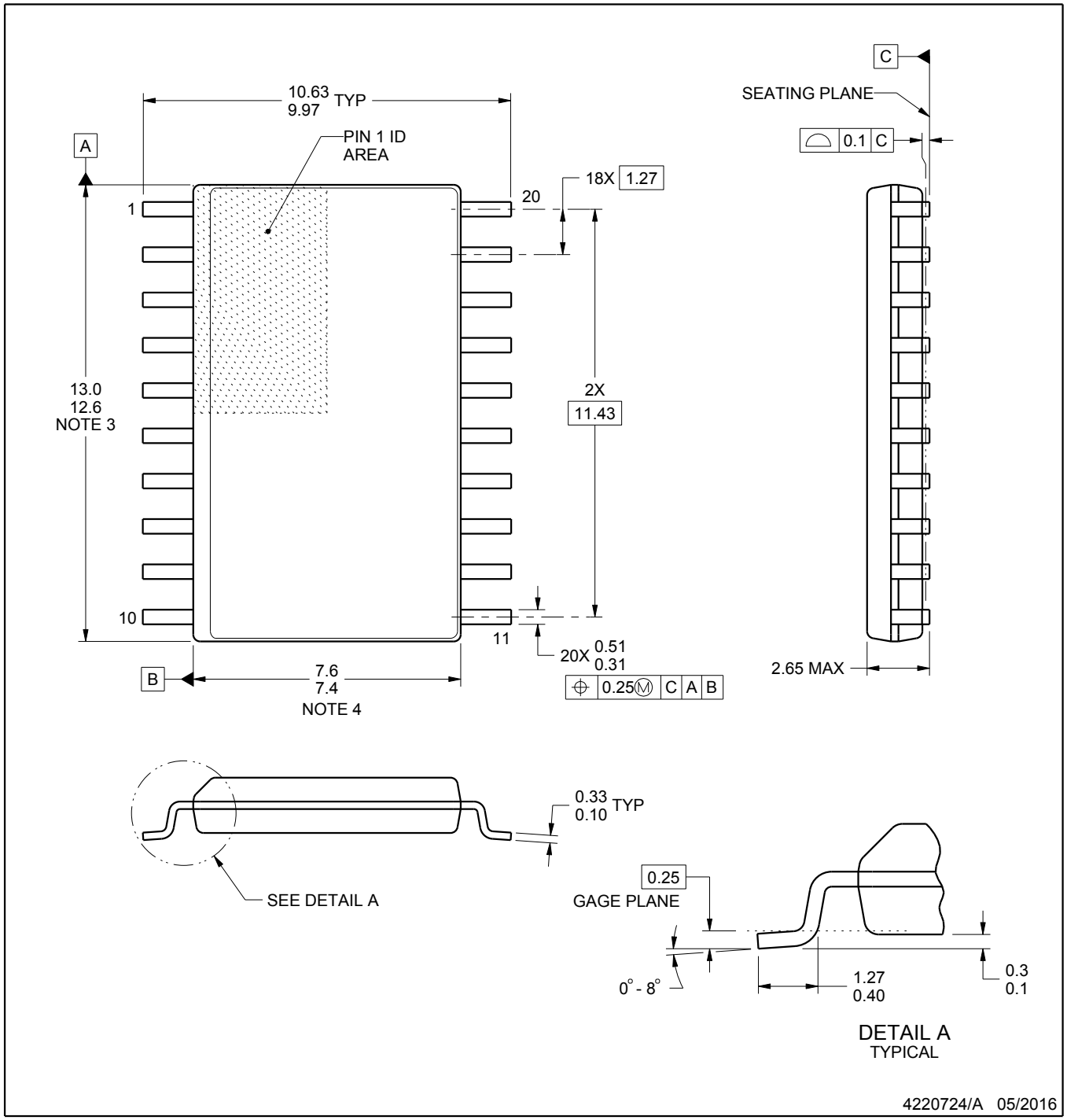


PACKAGE OUTLINE

DW0020A

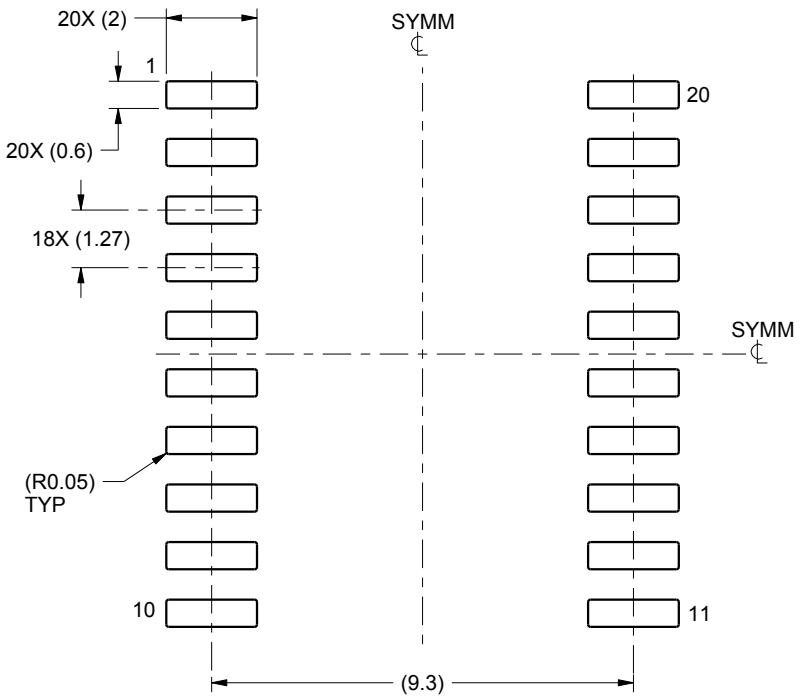
SOIC - 2.65 mm max height

SOIC

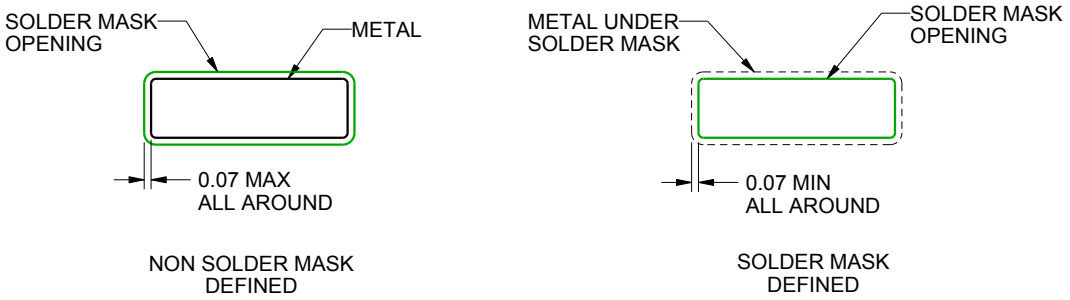


NOTES:

1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm per side.
5. Reference JEDEC registration MS-013.



LAND PATTERN EXAMPLE
SCALE:6X



SOLDER MASK DETAILS

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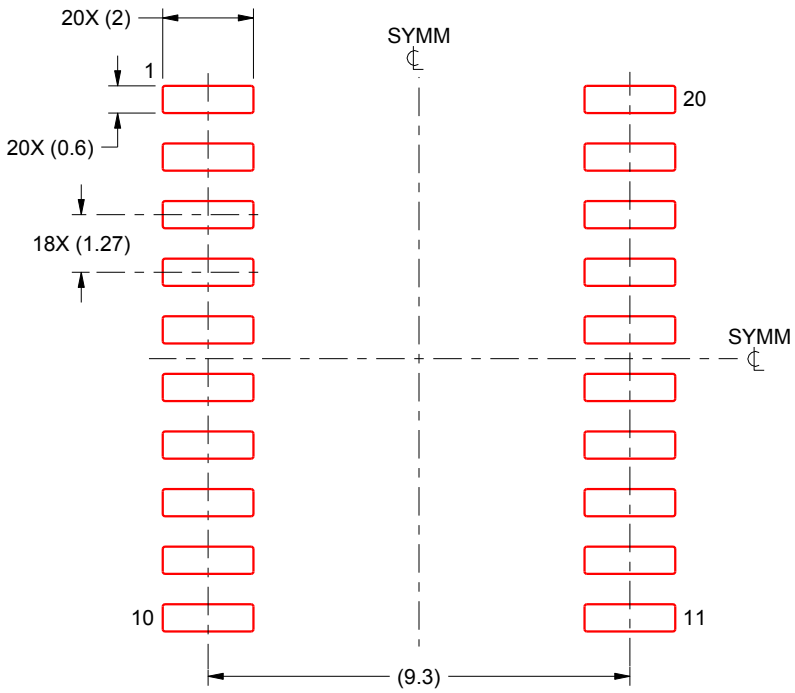
NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:6X

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NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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